

STA516B

60-V 6-A quad power half-bridge digital amplifier

Features

- Low input/output pulse width distortion
- 200 mΩ R_{dsON} complementary DMOS output stage
- CMOS-compatible logic inputs
- Thermal protection
- Thermal-warning output
- Undervoltage protection

Description

STA516B is a monolithic quad half-bridge power amplifier in Multipower BCD Technology. The device can be used as a dual-bridge stage or reconfigured, by connecting pin CONFIG to pins VDD, as a single-bridge stage with double-current capability or as a half-bridge stage (binary mode) with half-current capability.

The device is designed, particularly, to be the output stage of a stereo all-digital high-efficiency amplifier. It is capable of delivering 160 W + 160 W into 8- Ω loads with THD = 10% at V_{CC} = 51 V or, in single-BTL configuration, 320 W into a 4- Ω load with THD = 10% at V_{CC} = 52 V.

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PowerSO36 package with exposed pad up

The input pins have a threshold proportional to the voltage on pin VL.

The STA516B is aimed at audio amplifiers in Hi-Fi applications, such as home theatre systems, active speakers and docking stations.

It comes in a 36-pin PowerSO package with exposed pad up (EPU).

Order code Temperature range		Package	Packaging
STA516B	0 to 70 °C	PowerSO36 EPU	Tube
STA516B13TR	0 to 70 °C	PowerSO36 EPU	Tape and reel

Table 1. Device summary

1 Introduction

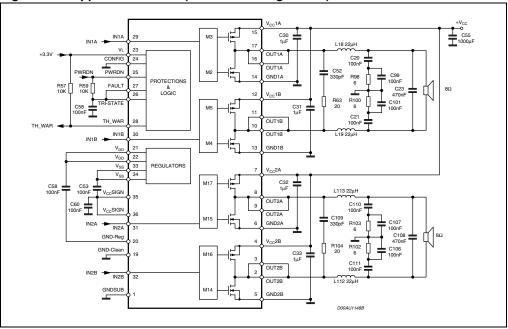


Figure 1. Application circuit (dual-BTL configuration)



2 Pin description



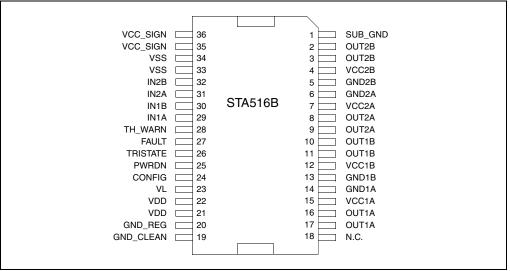


Table 2. Pin function

Pin	Name	Туре	Description	
1	GND_SUB	PWR	Substrate ground	
2, 3	OUT2B	0	Half-bridge stage output 2B	
4	VCC2B	PWR	Positive supply	
5	GND2B	PWR	Negative supply	
6	GND2A	PWR	Negative supply	
7	VCC2A	PWR	Positive supply	
8, 9	OUT2A	0	Half-bridge stage output 2A	
10, 11	OUT1B	0	Half-bridge stage output 1B	
12	VCC1B	PWR	Positive supply	
13	GND1B	PWR	Negative supply	
14	GND1A	PWR	Negative supply	
15	VCC1A	PWR	Positive supply	
16, 17	OUT1A	0	Half-bridge stage output 1A	
18	N.C.	-	No internal connection	
19	GND_CLEAN	PWR	Logical ground	
20	GND_REG	PWR	Ground for regulator V _{DD}	
21, 22	VDD	PWR	5-V regulator referred to ground	
23	VL	PWR	High logical state setting voltage, V_L	



Pin	Name	Туре	Description
24	CONFIG	I	Configuration pin: 0: normal operation 1: bridges in parallel (OUT1A = OUT1B, OUT2A = OUT2B (If IN1A = IN1B, IN2A = IN2B))
25	PWRDN	I	Standby pin: 0: low-power mode 1: normal operation
26	TRISTATE	1	3-state pin:0: all power amplifier outputs in high-impedance state1: normal operation
27	FAULT	0	Fault advisor (open-drain device, needs pullup resistor): 0: fault detected (short circuit or thermal, for example) 1: normal operation
28	TH_WARN	0	Thermal-warning advisor (open-drain device, needs pullup resistor): 0: temperature of the IC >130 ^o C 1: normal operation
29	IN1A	I	Half-bridge stage input 1A
30	IN1B	I	Half-bridge stage input 1B
31	IN2A	I	Half-bridge stage input 2A
32	IN2B	I	Half-bridge stage input 2B
33, 34	VSS	PWR	5-V regulator referred to +V _{CC}
35, 36	VCC_SIGN	PWR	Signal positive supply

 Table 2.
 Pin function (continued)



3 Electrical characteristics

Table 3. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CC}	DC supply voltage (pins 4, 7, 12, 15)	60	V
V _{max}	Voltage on pins 23 to 32	5.5	V
T _{op}	Operating temperature range	0 to 70	°C
T _{stg} , T _j	Storage and junction temperatures	-40 to 150	°C

Table 4. Thermal data

Symbol	Parameter	Min	Тур	Max	Unit
T _{j-case}	Thermal resistance junction to case (thermal pad)	-	1	2.5	°C/W
T _{jSD}	Thermal-shutdown junction temperature	-	150	-	°C
T _{warn}	Thermal-warning temperature	-	130	-	°C
t _{hSD}	Thermal-shutdown hysteresis	-	25	-	°C

Unless otherwise stated, the test conditions for Table 5 below are V_L = 3.3 V, V_{CC} = 50 V and T_{amb} = 25 $^\circ C$

Symbol	Parameter Test conditions		Min	Тур	Max	Unit
R _{dsON}	Power P-channel/N-channel MOSFET R _{dsON}	I _{dd} = 1 A	-	200	240	mΩ
I _{dss}	Power P-channel/N-channel leakage Idss	-	-	-	100	μA
ЯN	Power P-channel R _{dsON} matching	$I_{dd} = 1 A$	95	-	-	%
gР	Power N-channel R _{dsON} matching	I _{dd} = 1 A	95	-	-	%
Dt_s	Low current dead time (static)	see Figure 3	-	10	20	ns
Dt_d	High current dead time (dynamic)	$\begin{array}{l} L=22 \ \mu \text{H}, \ C=470 \ \text{nF} \\ \text{R}_{L}=8 \ \Omega, \ \text{I}_{dd}=4.5 \ \text{A} \\ \text{see Figure 4} \end{array}$	-	-	50	ns
t _{d ON}	Turn-on delay time	Resistive load	-	-	100	ns
t _{d OFF}	Turn-off delay time	Resistive load	-	-	100	ns
t _r	Rise time	Resistive load see <i>Figure 3</i>	-	-	25	ns
t _f	Fall time	Resistive load see <i>Figure 3</i>	-	-	25	ns
V _{CC}	Supply operating voltage	-	10	-	56	V

Table 5. Electrical characteristics



Symbol	Parameter	Test conditions	Min	Тур	Мах	Unit
V _{IN-High}	High-level input voltage	-	-	-	V _L /2 + 300 mV	v
V _{IN-Low}	Low-level input voltage	-	V _L / 2 - 300 mV	-	-	v
I _{IN-H}	High-level input current	$V_{IN} = V_L$	-	1	-	μA
I _{IN-L}	Low-level input current	V _{IN} = 0.3 V	-	1	-	μA
I _{PWRDN-H}	High-level PWRDN pin input current	V _L = 3.3 V	-	35	-	μA
V _{Low}	Logical low-state voltage (pins PWRDN, TRISTATE) (see <i>Table 6</i>)	V _L = 3.3 V	0.8	-		v
V _{High}	Logical high-state voltage (pins PWRDN, TRISTATE) (see <i>Table 6</i>)	V _L = 3.3 V		-	1.7	v
I _{VCC-} PWRDN	Supply current from V _{CC} in power down	V _{PWRDN} = 0 V	-	-	3	mA
I _{FAULT}	Output current on pins FAULT, TH_WARN with fault condition	V _{pin} = 3.3 V	-	1	-	mA
I _{VCC-HiZ}	Supply current from V _{CC} in 3-state	V _{TRISTATE} = 0 V	-	22	-	mA
I _{VCC}	Supply current from V _{CC} in operation both channels switching)	Input pulse width = 50% duty, switching frequency = 384 kHz, no LC filters	-	70	-	mA
I _{OCP}	Overcurrent protection threshold (short-circuit current limit) ⁽¹⁾	-	6	8	10	A
V _{UVP}	Undervoltage protection threshold	-	-	7	-	v
V _{OVP}	Overvoltage protection threshold	-	60	-	70	v
t _{pw_min}	Minimum output pulse width	No load	25	-	40	ns

 Table 5.
 Electrical characteristics (continued)

1. See specific application note number: AN1994

Table 6.	Threshold switching voltage variation with voltage on pin VL
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Voltage on pin VL, V_L	V _{LOW} max	V _{HIGH} min	Unit
2.7	0.7	1.5	V
3.3	0.8	1.7	V
5.0	0.85	1.85	V



	Logic tru						
Pin Inputs as per <i>Figure 4</i>			Transistors as per <i>Figure 4</i>				Output mode
TRISTATE	INxA	INxB	Q1	Q2	Q3	Q4	Output mode
0	x	х	Off	Off	Off	Off	Hi Z
1	0	0	Off	Off	On	On	Dump
1	0	1	Off	On	On	Off	Negative
1	1	0	On	Off	Off	On	Positive
1	1	1	On	On	Off	Off	Not used

Table 7. Logic truth table

3.1 Test circuits



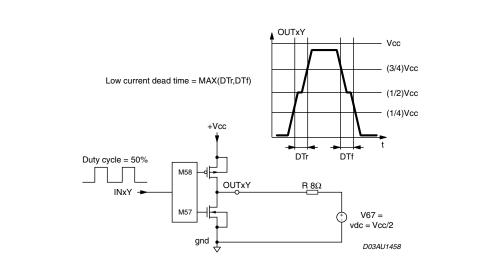
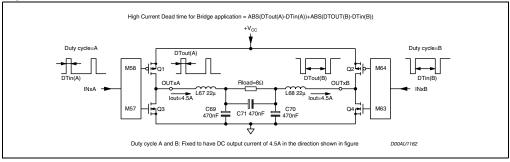


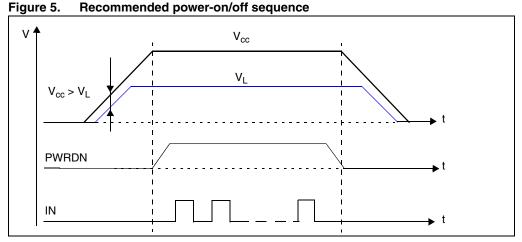
Figure 4. Current dead-time test circuit





4 Power supply and control sequencing

To guarantee correct operation and reliability, the recommended power-on/off sequence as shown in *Figure 5* must be followed.



 V_{CC} must turn on before V_L . This prevents uncontrolled current flowing through the internal protection diode connected between V_L (logic supply) and V_{CC} (high power supply) which could result in damage to the device.

PWRDN must be released after V_L is switched on. An input signal can then be applied to the power stage.



5 Applications

Figure 6 below shows a single-BLT configuration capable of giving 320 W into a 4- Ω load at 10% THD with V_{CC} = 52 V. This result was obtained using the STA30X+STA50X demonstration board. Note that a PWM modulator as driver is required.

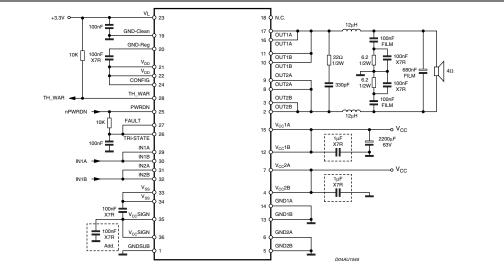
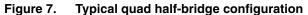
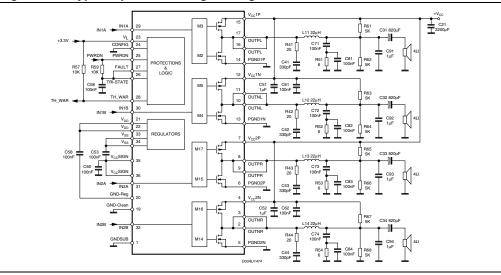


Figure 6. Typical single-BTL configuration for 320 W

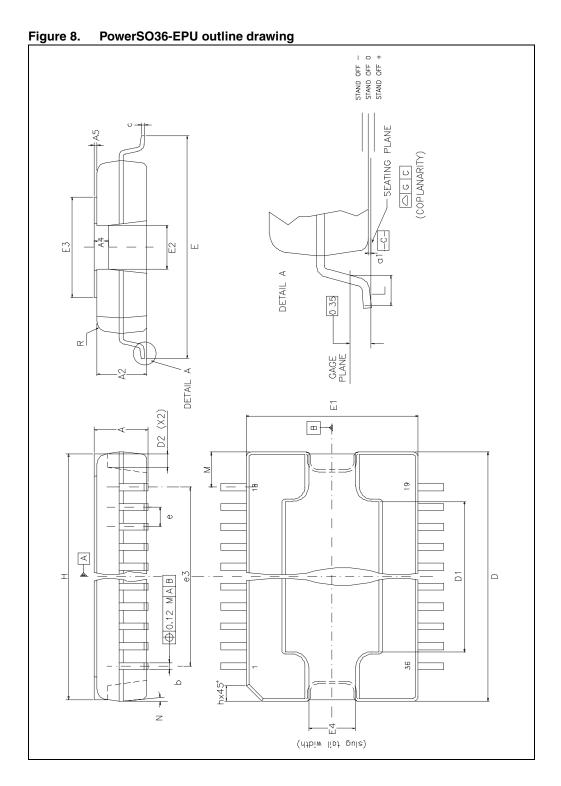




For more information, refer to the application note AN1994.



6 Package mechanical data



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Table 8.	PowerS	O36-EPU dim	nensions			
Symbol		mm			inch	
Symbol	Min	Тур	Max	Min	Тур	Max
A	3.25	-	3.43	0.128	-	0.135
A2	3.10	-	3.20	0.122	-	0.126
A4	0.80	-	1.00	0.031	-	0.039
A5	-	0.20	-	-	0.008	-
a1	0.03	-	-0.04	0.001	-	-0.002
b	0.22	-	0.38	0.009	-	0.015
с	0.23	-	0.32	0.009	-	0.013
D	15.80	-	16.00	0.622	-	0.630
D1	9.40	-	9.80	0.370	-	0.386
D2	-	1.00	-	-	0.039	-
E	13.90	-	14.50	0.547	-	0.571
E1	10.90	-	11.10	0.429	-	0.437
E2	-	-	2.90	-	-	0.114
E3	5.80	-	6.20	0.228	-	0.244
E4	2.90	-	3.20	0.114	-	0.126
е	-	0.65	-	-	0.026	-
e3	-	11.05	-	-	0.435	-
G	0	-	0.08	0	-	0.003
н	15.50	-	15.90	0.610	-	0.626
h	-	-	1.10	-	-	0.043
L	0.80	-	1.10	0.031	-	0.043
М	2.25	-	2.60	0.089	-	0.102
N	-	-	10 degrees	-	-	10 degrees
R	-	0.6	-	-	0.024	-
S	-	-	8 degrees	-	-	8 degrees

 Table 8.
 PowerSO36-EPU dimensions

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.



7 Revision history

Table 9.Document revision history

Date	Revision	Changes
01-Feb-2007	1	Initial release.
19-Mar-2007	2	Update to reflect product maturity.
12-Aug-2009	3	Updated description section on cover page.

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